

$$i_1 = \frac{I_T}{2} - \frac{\sqrt{2} I_T \beta}{2} \cdot v_d \sqrt{1 - \left(\frac{v_d^2 \beta^2}{2 I_T} \right)}$$

$$i_2 = \frac{I_T}{2} + \frac{\sqrt{2} I_T \beta}{2} v_d \sqrt{1 - \left(\frac{v_d^2 \beta^2}{2 I_T} \right)}$$

$$i_0 = i_2 - i_1 = \underbrace{\sqrt{2} I_T \beta}_{G_0} v_d \sqrt{1 - \left(\frac{v_d^2 \beta^2}{2 I_T} \right)}$$

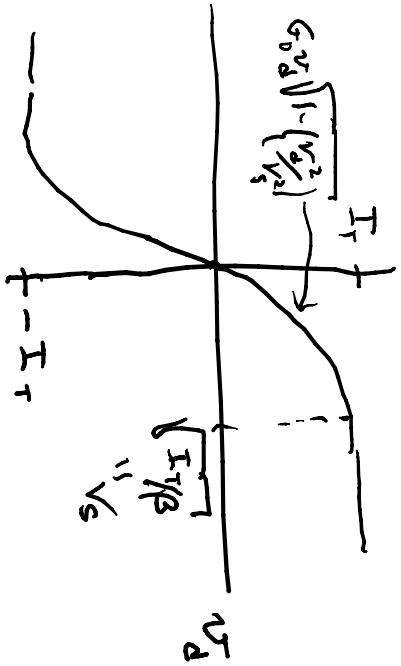
this approx $\sqrt{1 - \dots}$
if v_d is very large

$$\text{max } i_0 \Rightarrow \frac{d i_0}{d v_d} = G_0 \left[\sqrt{1 - \left(\frac{v_d^2 \beta^2}{2 I_T} \right)} + \frac{v_d \cdot \frac{1}{2} \left(-2 v_d \beta^2 / 2 I_T \right)}{\sqrt{1 - \left(\frac{v_d^2 \beta^2}{2 I_T} \right)}} \right]$$

$$= \frac{G_0}{\sqrt{1 - (\dots)}} \left[1 - \left(\frac{v_d^2 \beta^2}{2 I_T} \right) - \frac{v_d^2 \beta^2}{2 I_T} \right] = \frac{G_0}{\sqrt{1 - (\dots)}} \left[1 - 1 \frac{v_d^2 \beta^2}{I_T} \right]$$

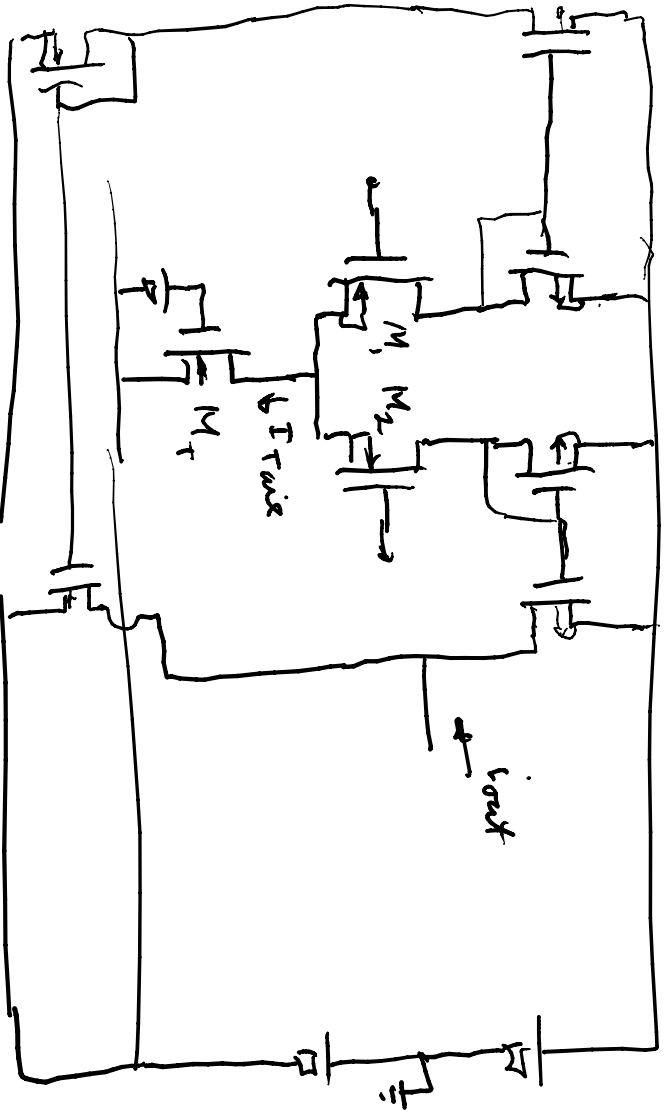
$$= 0 \Rightarrow v_d^2 = \frac{1}{\beta} \frac{I_T}{\beta}, \quad v_d = \pm \sqrt{\frac{I_T}{\beta}}$$

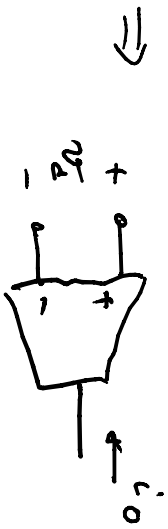
$$i_0 = G_0 \left[\sqrt{\frac{I_T}{\beta}} \cdot \sqrt{1 - \frac{1}{2}} \right] = G_0 \cdot \sqrt{\frac{I_T}{\beta}} \cdot \frac{1}{\sqrt{2}} = \sqrt{\frac{2 I_T \beta}{\beta}} \cdot \frac{1}{\sqrt{2}} = I_T$$



$$\beta = \frac{K_P W}{2 L}$$

note I_T can vary with a voltage on the gate of its transistors





OTA

6th edition
MOS picture p. 233

BJT ⇒ Ebers-Moll equation
describer B9

ECL r. 1180

⇒ Hummel-Born
(used by Kravis) B11

Pass transistors r. 1153

MOS threshold voltage p. 324

$$V_{th} = V_{TD} + \gamma \left(\sqrt{2q_f + V_{SB}} - \sqrt{2q_f} \right)$$

n channel
 $2q_f \approx 0.6$

$$\begin{aligned} \beta &= 5 \\ &= V_{TD} - \delta \left(\sqrt{2q_f + |V_{SB}|} - \sqrt{2q_f} \right) \end{aligned}$$

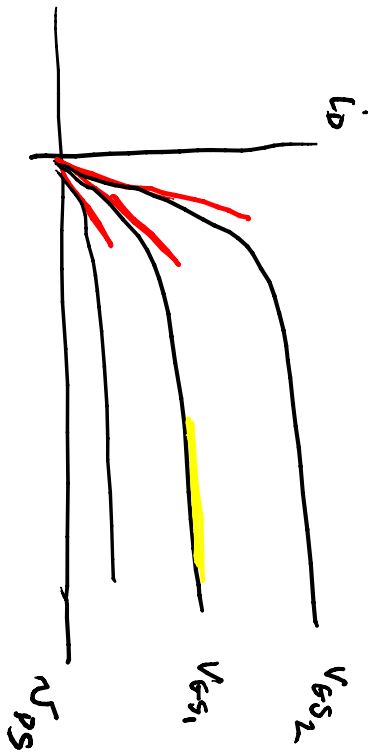
p channel
 $2q_f \approx 3/4$

MOS, NMOS

0 out. off. $V_{GS} < V_{th}$

$$i_D = \frac{K_n W L}{2 L} \begin{cases} 0 & \text{out. off. } V_{GS} < V_{th} \\ 2(V_{GS} - V_{th})V_{DS} - V_{DS}^2 & (1 + \gamma V_{DS}), \quad V_{GS} \geq V_{th}, V_{GS} - V_{th} \geq V_{DS} \\ (V_{GS} - V_{th})^2 & (1 + \gamma V_{DS}) \text{ saturation, } 0 \leq V_{GS} - V_{th} \leq V_{DS} \end{cases}$$

ohmic
 $V_{GS} \geq V_{th}, V_{GS} - V_{th} \geq V_{DS}$

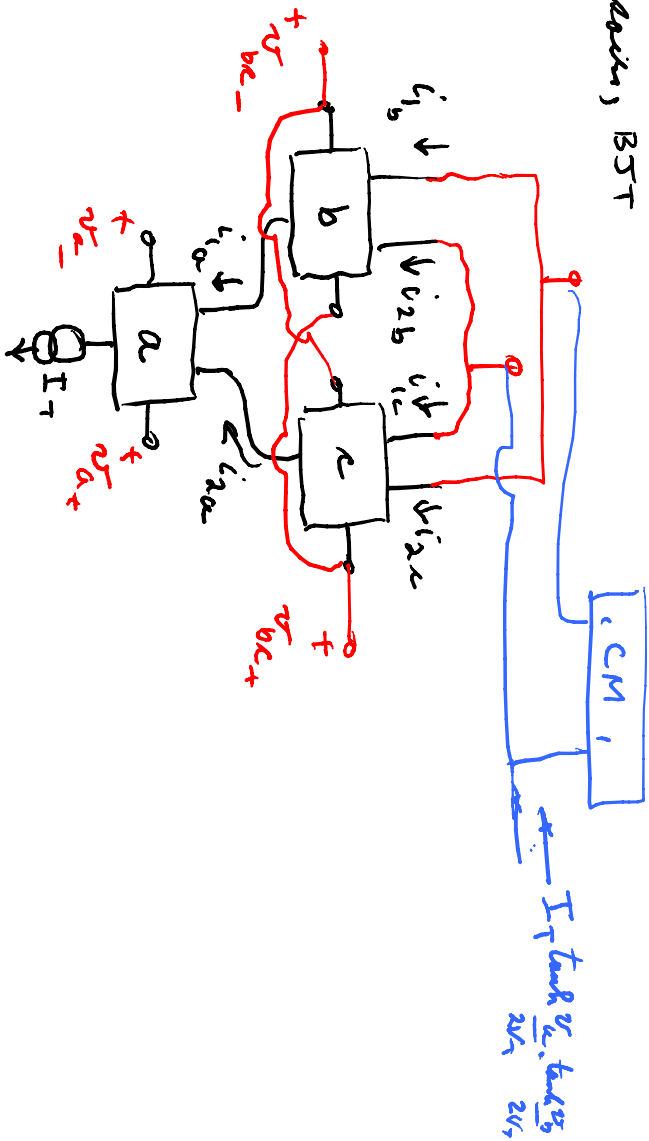


$$\left. \frac{di_D}{dv_{DS}} \right|_{v_{DS}=0} = \frac{d}{dv_{DS}} \Rightarrow \left. \frac{K_P W}{2 L} \{ 2(v_{GS} - V_{th}) - 2v_{DS}^2 \} \right|_{v_{DS}=0}$$

$$\text{Along } G_1 = (K_P W/L) (v_{GS} - V_{th})$$

here $i_D \approx \frac{K_P W}{2 L} (2(v_{GS} - V_{th})v_{DS} = G_1 \cdot v_{DS}, \quad v_{DS} > 0$

3-diff pairs, BST



$$i_{2a} - i_{1a} = i_{0a} = I_T \tanh(v_a / 2V_T)$$

$$i_{2b} - i_{1b} = i_{0b} = i_{0a} \tanh(v_b / 2V_T) \quad i_{2c} - i_{1c} = i_{0a} \tanh(v_c / 2V_T) = i_{0c}$$

$$\text{source } v_c = v_b = v_{0a}$$

$$\text{And hence } i_{0b} - i_{0c} = (i_{1a} - i_{2a}) \tanh(v_0 / 2V_T)$$

$$= I_T \tanh(v_a / 2V_T) \tanh(v_0 / 2V_T) \approx I_T \frac{v_a}{2V_T} \cdot \frac{v_0}{2V_T}$$

$$i_{0b} - i_{0c} = i_{2b} - i_{1b} - (i_{2c} - i_{1c}) = (i_{2b} + i_{1c}) - (i_{1b} + i_{2c})$$